

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-53. (canceled)

54. (currently amended) An active matrix addressing LCD device comprising:

an active matrix substrate having a transparent, dielectric plate, thin film transistors (TFTs) arranged on the plate, and pixel electrodes arranged on the plate;

wherein the active matrix substrate includes at least one of scan lines, signal lines, and common lines, each of the lines having a multilevel conductive structure at a respective terminal thereof;

wherein the multilevel conductive structure comprises a TiN film having a nitrogen concentration of 25 atomic % or higher, the TiN film being located at a top of the multilevel conductive structure; and

wherein a transparent conductive film is absent from the TiN film so that the TiN film is exposed at each said terminal.

55. (previously presented) The device according to

claim 54, wherein the multilevel conductive structure comprises an Al-based film located below the TiN film, and at least one Ti film located at least at one of an upper position and a lower position with respect to the Al-based film.

56. (previously presented) The device according to claim 55, wherein each of the lines has a same multilevel conductive structure not only at the respective terminal, but also in the remaining parts thereof.

57. (previously presented) The device according to claim 55, wherein the multilevel conductive structure is a three-level structure formed by the TiN film located at the top, the Ti film located at the middle, and the Al-based film located at the bottom.

58. (previously presented) The device according to claim 55, wherein the multilevel conductive structure is a three-level structure formed by the TiN film located at the top, the Al-based film located at the middle, and the Ti film located at the bottom.

59. (previously presented) The device according to claim 55, wherein the multilevel conductive structure is a four-level structure formed by the TiN film located at the top, the Ti film located at the upper middle, the Al-based film located at the lower middle, and the Ti film located at the bottom.

60. (previously presented) The device according to claim 55, wherein the Al-based film is made of Al, or an Al alloy including Al as its main ingredient.